



DMG3404L

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
2017	25mΩ @ V <sub>GS</sub> = 10V	5.8A
30V	35mΩ @ V <sub>GS</sub> = 4.5V	4.8A

# **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Charging
- Power Management Functions
- DC-DC Converters
- Portable Power Adaptors

#### N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features and Benefits**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

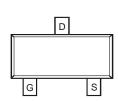
## **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Terminals Connections: See Diagram Below
- Weight: 0.009138 grams (Approximate)



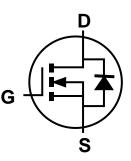
SOT23

Top View



Top View

Pin Configuration



Equivalent Circuit

### Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3404L-7	SOT23	3000/Tape & Reel
DMG3404L-13	SOT23	10000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

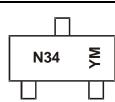
Notes:

See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and</li>

<1000ppm antimony compounds.</p>

For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



N34 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key

Year	2012	2	2013	2014		2015	2016		2017	2018		2019
Code	Z		А	В		С	D		E	F		G
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	30	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 5) $V_{GS}$ = 10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	4.2 3.5	A
Continuous Drain Current (Note 6) $V_{GS}$ = 10V	I <sub>D</sub>	5.8 4.9	A		
Pulsed Drain Current (Pulse Width ≤10µS, Duty	Cycle ≤1%)		IDM	30	А

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	0.78	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	164	°C/W
Power Dissipation (Note 6)	PD	1.33	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	96	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

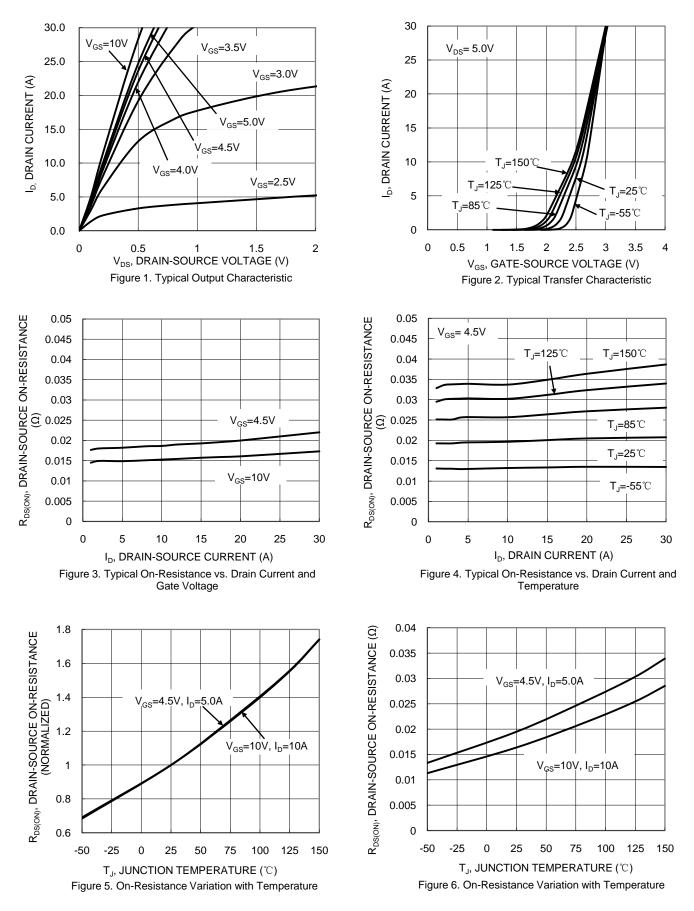
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						•
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30			V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	_		1.0	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						·
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.0	1.5	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
Static Drain-Source On-Resistance		_	21	25	mΩ	$V_{GS} = 10V, I_D = 5.8A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	24	35	11122	$V_{GS} = 4.5 V, I_D = 4.8 A$
Diode Forward Voltage	V <sub>SD</sub>	_	0.75	1.0	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						·
Input Capacitance	Ciss		641	—	pF	
Output Capacitance	C <sub>oss</sub>	_	66	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	51		pF	1 = 1.0MHZ
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Qq	_	13.2		nC	
Gate-Source Charge	Q <sub>gs</sub>	_	1.7	_	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 5.8A
Gate-Drain Charge	Q <sub>qd</sub>	_	2.2		nC	
Turn-On Delay Time	t <sub>D(ON)</sub>		3.3		ns	
Turn-On Rise Time	t <sub>R</sub>		4.4		ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V,
Turn-Off Delay Time	t <sub>D(OFF)</sub>		22	—	ns	$R_L = 1.25\Omega, R_g = 3\Omega$
Turn-Off Fall Time	t <sub>F</sub>	_	5.2		ns	

Notes:

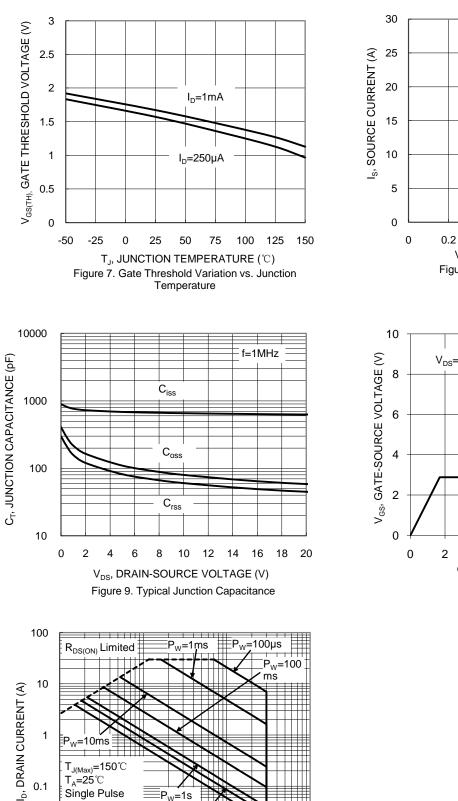
Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

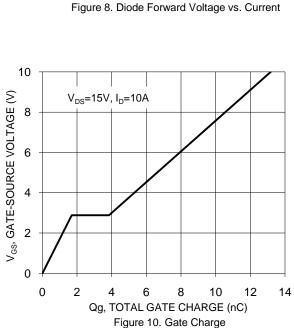


## DMG3404L









 $V_{GS}$ =0V,  $T_A$ =25 $^{\circ}$ C

0.6

V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V)

0.8

1

1.2

0.4

**T<sub>A</sub>=25℃** 

Single Pulse

DUT on 1\*MRP Board

=1s

V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 11. SOA, Safe Operation Area

1

w=10s

DĊ 

10

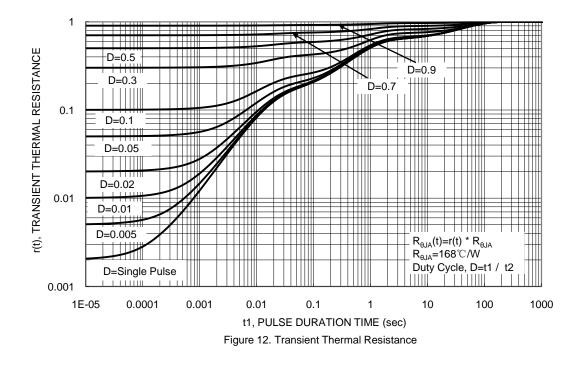
0.1

0.01

0.1

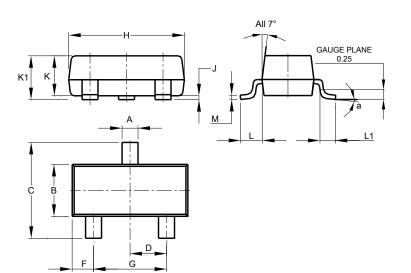
100





# **Package Outline Dimensions**

Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.



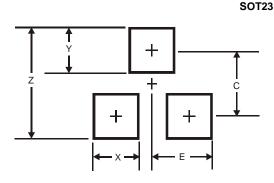
	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
Μ	0.085	0.150	0.110					
а	8°							
All	All Dimensions in mm							

SOT23



## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/\_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35

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